Guoqiang Zhang

List of Publications by Year
in descending order

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43 papers	753 citations	516561 16 h-index	526166 27 g-index
43 all docs	43 docs citations	43 times ranked	913 citing authors

#	Article	IF	Citations
1	Monolithic lateral pâ€“n junction GaAs nanowire diodes via selective lateral epitaxy. Nanotechnology, 2021, 32, 505203.	1.3	2
2	Thermal effect of InP/InAs nanowire lasers integrated on different optical platforms. OSA Continuum, 2021, 4, 1838.	1.8	7
3	InP/InAs Quantum Heterostructure Nanowires Toward Telecom-Band Nanowire Lasers. , 2021, , 433-454.		1
4	Hybrid Nanowire Photodetector Integrated in a Silicon Photonic Crystal. ACS Photonics, 2020, 7, 3467-3473.	3.2	15
5	Nanowire photonics toward wide wavelength range and subwavelength confinement [Invited]. Optical Materials Express, 2020, 10, 2560.	1.6	10
6	Nanowire-based telecom-band light-emitting diodes with efficient light extraction. Japanese Journal of Applied Physics, 2020, 59, 105003.	0.8	5
7	Near-field cavity optomechanical coupling in a compound semiconductor nanowire. Communications Physics, 2020, 3, .	2.0	4
8	Mid-Infrared Lasing of Single Wurtzite InAs Nanowire. Nano Letters, 2019, 19, 8059-8065.	4.5	22
9	Telecom-band lasing in single InP/InAs heterostructure nanowires at room temperature. Science Advances, 2019, 5, eaat8896.	4.7	68
10	Wurtzite GaP nanowire grown by using tertiarybutylchloride and used to fabricate solar cell. Japanese Journal of Applied Physics, 2019, 58, 015004.	0.8	1
11	Diameter-tailored telecom-band luminescence in InP/InAs heterostructure nanowires grown on InP (111)B substrate with continuously-modulated diameter from microscale to nanoscale. Nanotechnology, 2018, 29, 155202.	1.3	9
12	Alternating InAsP/InP heterostructure nanowires grown with tertiary-butyl chloride. Nano Futures, 2018, 2, 045006.	1.0	8
13	Direct modulation of a single InP/InAs nanowire light-emitting diode. Applied Physics Letters, 2018, 112, .	1.5	21
14	Subwavelength Nanowire Lasers on a Silicon Photonic Crystal Operating at Telecom Wavelengths. ACS Photonics, 2017, 4, 355-362.	3.2	35
15	Continuous-wave operation and 10-Gb/s direct modulation of InAsP/InP sub-wavelength nanowire laser on silicon photonic crystal. APL Photonics, 2017, 2, .	3.0	60
16	Nanowire-nanoantenna coupled system fabricated by nanomanipulation. Optics Express, 2016, 24, 8647.	1.7	12
17	Self-aligned gate-all-around InAs/InP coreâ€“shell nanowire field-effect transistors. Japanese Journal of Applied Physics, 2015, 54, 04DN04.	0.8	5
18	Controlled 1.1â€“1.6Î¼m luminescence in gold-free multi-stacked InAs/InP heterostructure nanowires. Nanotechnology, 2015, 26, 115704.	1.3	16

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19	Bridging the Gap between the Nanometer-Scale Bottom-Up and Micrometer-Scale Top-Down Approaches for Site-Defined InP/InAs Nanowires. ACS Nano, 2015, 9, 10580-10589.	7.3	17
20	Growth of InP nanowires on graphene-covered Fe. Japanese Journal of Applied Physics, 2014, 53, 015504.	0.8	3
21	Movable high-Q nanoresonators realized by semiconductor nanowires on a Si photonic crystal platform. Nature Materials, 2014, 13, 279-285.	13.3	94
22	TBCl etching for uniform-diameter InAsP nanowires. , 2014, , .		0
23	Etching effect of tertiary-butyl chloride during InP-nanowire growth. Journal of Crystal Growth, 2014, 402, 299-303.	0.7	4
24	Semiconductor Nanowire Induced Photonic-Crystal Nanocavity with Selectable Resonant Wavelength. , 2014, , .		0
25	Encapsulated gate-all-around InAs nanowire field-effect transistors. Applied Physics Letters, 2013, 103, .	1.5	18
26	Au-free InAs nanowires grown in In-particle-assisted vapor-liquid-solid mode: growth, structure, and electrical property. AIP Advances, 2013, 3, .	0.6	23
27	Vertically Aligned InP Nanowires Grown via the Self-Assisted Vaporâ€“Liquidâ€“Solid Mode. Applied Physics Express, 2012, 5, 055201.	1.1	18
28	VLS Growth of Alternating InAsP/InP Heterostructure Nanowires for Multiple-Quantum-Dot Structures. Nano Letters, 2012, 12, 2888-2893.	4.5	52
29	Flat-Top and Stacking-Fault-Free GaAs-Related Nanopillars Grown on Si Substrates. Journal of Nanotechnology, 2012, 2012, 1-8.	1.5	3
30	Predominant Si Doping through Au Catalyst Particles in the Vaporâ”Liquidâ”Solid Mode over the Shell Layer via the Vapor-Phase Epitaxy Mode of InAs Nanowires. Journal of Physical Chemistry C, 2011, 115, 2923-2930.	1.5	9
31	Supercurrent through InAs nanowires with highly transparent superconducting contacts. Nanotechnology, 2011, 22, 445701.	1.3	25
32	<110>-Oriented In0.04Ga0.96As Nanowires Laterally Grown on GaAs (311)B Substrate in Au-Catalyzed Vaporâ€“Liquidâ€“Solid Mode. Applied Physics Express, 2010, 3, 105002.	1.1	3
33	Structural, Compositional, and Optical Characterizations of Vertically Aligned AlAs/GaAs/GaP Heterostructure Nanowires Epitaxially Grown on Si Substrate. Japanese Journal of Applied Physics, 2010, 49, 015001.	0.8	24
34	Parallel-aligned GaAs nanowires with âŸ¨110âŸ© orientation laterally grown on [311]B substrates via the gold-catalyzed vaporâ€“liquidâ€“solid mode. Nanotechnology, 2010, 21, 095607.	1.3	16
35	Synthesis of GaAs nanowires with very small diameters and their optical properties with the radial quantum-confinement effect. Applied Physics Letters, 2009, 95, 123104.	1.5	39
36	Photoluminescence study of bare freestanding gallium arsenide nanowires grown by vapor-liquid-solid method. , 2009, , .		0

#	Article	IF	Citations
37	Heterostructures in GaP-based free-standing nanowires on Si substrates. , 2009, , .		0
38	Growth of GaInAs/AlInAs Heterostructure Nanowires for Long-Wavelength Photon Emission. Nano Letters, 2008, 8, 3645-3650.	4.5	23
39	Vertically Aligned GaP/GaAs Core-Multishell Nanowires Epitaxially Grown on Si Substrate. Applied Physics Express, 2008, 1, 064003.	1.1	28
40	Very Thin Single-Walled Carbon Nanotubes Self-Assembled on 6H-SiC($000ar{1}$) Substrate by Surface Decomposition Method. Japanese Journal of Applied Physics, 2007, 46, L53-L56.	0.8	5
41	Bending at Thinned GaAs Nodes in GaP-based Free-standing Nanowires. Japanese Journal of Applied Physics, 2007, 46, L780-L782.	0.8	7
42	Vertically Aligned Single-Crystal ZnO Nanotubes Grown on Î³-LiAlO2(100) Substrate by Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2007, 46, L730-L732.	0.8	18
43	Au-assisted growth approach for vertically aligned ZnO nanowires on Si substrate. Applied Physics Letters, 2006, 89, 113112.	1.5	23